



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Steven T. Harshfield, et al.

Serial No.: 09/853,233

Filed: May 11, 2001

For: PCRAM MEMORY CELL AND
METHOD OF MAKING SAME

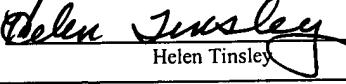
§ Group Art Unit: 2823
§ Examiner: Coleman, W.
§ Atty Docket: MICS:0061/FLE
§ 00-0535
§

Assistant Commissioner
for Patents
Washington, D.C. 20231

Sir:

CERTIFICATE OF MAILING
37 C.F.R. 1.8

I hereby certify that this correspondence is being deposited with the U.S. Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on the date below:

December 4, 2002 
Date Helen Tinsley

AMENDMENT AND RESPONSE

In response to the Office Action mailed September 4, 2002, please amend the subject
Application, as follows:

IN THE CLAIMS

 Please cancel claims 4, 22, 27, 34 and 41, without prejudice.

Please amend claims 1, 17-21, 26, 31 and 38, as follows:

1. (Once Amended) A memory cell comprising:

B1
a first line formed over a substrate, the first line being formed of a first conductive
material that comprises one of aluminum, copper, nickel, and tungsten;

5/B 2823
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